

Defects and Properties of Semiconductors: Defect Engineering

Edited by

J. Chikawa, K. Sumino, and K. Wada

The logo consists of the letters "ASST" in a bold, sans-serif font, centered between two thick, light blue horizontal bars. Each bar has a triangular arrow pointing towards the center of the logo.

ADVANCES IN SOLID STATE TECHNOLOGY

KTK Scientific Publishers/Tokyo

D. Reidel Publishing Company/Dordrecht, Boston, Lancaster, Tokyo

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